

METHOD FOR MANUFACTURING SEMICONDUCTOR DEVICE

BACKGROUND OF THE INVENTION

Field of the Invention

5 The present invention relates to a method for manufacturing a semiconductor device such as a MOS FET, and especially to a method for manufacturing a semiconductor device including a step of forming an aluminum-containing thin film so as to fill therewith
10 a minute contact hole formed on a semiconductor substrate such as a silicon substrate.

Description of Related Art

 In the process of manufacturing a semiconductor device, an electrode thin film of aluminum is formed
15 so as to fill therewith a hole-shaped or trench-shaped minute contact hole formed on a semiconductor substrate. Such an electrode thin film functions as a deriving electrode of a device (for example, transistor) formed on the silicon
20 substrate.

 Such a thin film has been heretofore formed by supplying aluminum atoms on a silicon substrate by sputtering method and forming an aluminum thin film so as to fill a contact hole therewith. In some cases,
25 in the step of forming the aluminum thin film, the

silicon substrate has been heated so that the contact hole can be easily filled with the aluminum thin film.

However, in keeping with wiring patterns recently becoming minute, the width and the diameter of a contact hole have become smaller (for example, not more than $0.6 \mu\text{m}$). On the other hand, the depth of a contact hole has not changed even if wiring patterns have become minute. Therefore, the ratio of the depth of a contact hole to the width or the diameter of the contact hole (aspect ratio) becomes large (for example, not less than 1).

An aluminum thin film capable of suitably filling such a contact hole having a small width or diameter and a large aspect ratio cannot be formed by the abovementioned conventional method. In concrete, there is a problem that a void (air gap) is formed in a portion of an aluminum thin film corresponding to the contact hole. It occurs because, by using sputtering method, the aluminum thin film grows to close the opening of the contact hole before the inner space of the contact hole having a small width or diameter and a large aspect ratio is completely filled with aluminum atoms.

Further, there is another problem that in the step of forming an aluminum thin film or the following

steps, aluminum atoms diffuse in diffusion regions or the like on the silicon substrate (aluminum spike) and thereby p-n junction of a device is destructed.

SUMMARY OF THE INVENTION

5 An object of the present invention is to provide a method for manufacturing a semiconductor device capable of suitably filling an aluminum-containing thin film into a contact hole having a small width or diameter and a large aspect ratio formed on a
10 semiconductor substrate.

Another object of the present invention is to provide a method for manufacturing a semiconductor device in which aluminum atoms are hard to diffuse from an aluminum-containing thin film filled into a
15 contact hole.

A method for manufacturing a semiconductor device according to the present invention is a method for manufacturing a semiconductor device having a semiconductor substrate with a contact hole filled
20 by an aluminum-containing thin film. This manufacturing method includes a step of forming a silicon-containing thin film so as to fill the contact hole on the surface of the semiconductor substrate, a step of removing the part of the
25 silicon-containing thin film outside the contact

hole, a step of forming an aluminum-containing thin film on the surface of the semiconductor substrate after completing the step of removing the part of the silicon-containing thin film, and a step of heating
5 the semiconductor substrate on which the aluminum-containing thin film is formed to such a temperature as to cause silicon to diffuse with respect to aluminum.

According to the present invention, prior to
10 forming an aluminum-containing thin film (hereinafter referred to as "aluminum thin film"), a silicon-containing thin film is formed so as to fill a contact hole. Aluminum atoms supplied onto the surface of the semiconductor substrate, for example,
15 by physical vapor deposition method in the following step of forming the aluminum thin film are also supplied onto the silicon-containing thin film formed so as to fill the contact hole.

In the step of heating the semiconductor
20 substrate, silicon atoms constituting the silicon-containing thin film in the contact hole diffuse in the aluminum thin film, and aluminum atoms constituting the aluminum thin film also diffuse in the silicon-containing thin film in the contact hole
25 to move into the contact hole.

As a result, the contact hole can be suitably filled with the aluminum thin film. Especially when the width or the diameter of the contact hole is as small as not more than $0.6\ \mu\text{m}$ and the aspect ratio of the contact hole is as high as not less than 1, such a manufacturing method is effective. Unnecessary portions of the aluminum thin film may be thereafter removed away by etching or the like. The aluminum thin film suitably filled into the contact hole can be obtained in such a manner.

The contact hole may be one for connecting a deriving electrode to a device formed on the surface of the semiconductor substrate or one for effecting inter-layer connection of multi-layer wirings. By the abovementioned method, for example, a semiconductor layer (possible to be the semiconductor substrate itself) exposed to the inside of the contact hole or wirings can be electrically connected to the aluminum thin film.

The step of heating the semiconductor substrate may be carried out at the same time with the step of forming the aluminum thin film or after completing the step of forming the aluminum thin film. Further, it is possible to carry out the step of heating the semiconductor substrate at the same time with the

step of forming the aluminum thin film and in addition continue the step of heating the semiconductor substrate for a predetermined time after completing the step of forming the aluminum thin film.

5 Furthermore, since the aluminum thin film becomes to contain silicon, aluminum atoms in the aluminum thin film filled into the contact hole are hard to diffuse in the semiconductor layer (especially one formed of silicon). As a result, p-n
10 junction formed in the inner portion of the semiconductor layer can be prevented from being destructed.

 The amount of silicon necessary for obtaining such an effect is as small as, for example, not more
15 than a few percent by atomic ratio to the amount of aluminum in the aluminum thin film. Therefore, the absolute amount of silicon supplied onto the surface of the semiconductor substrate in order to form a silicon-containing thin film so that it becomes
20 difficult to accurately control the amount of silicon.

 According to the present invention, the step of removing the part of the silicon-containing thin film is carried out so that the silicon-containing thin
25 film fills the contact hole and exists only in the

contact hole. Since the contact hole has a predetermined volume, the amount of the silicon-containing thin film or the amount of silicon in the silicon-containing thin film can be accurately
5 controlled.

The step of forming the silicon-containing thin film may be one for forming a silicon-containing thin film on the whole surface of the semiconductor substrate in which the contact hole is formed. The
10 semiconductor substrate may be, for example, a silicon substrate or a substrate on which an epitaxial layer is formed. The step of removing the part of the silicon-containing thin film may include a step of removing the part of the silicon-containing
15 thin film outside the contact hole by etching back. The step of removing the part of the silicon-containing thin film may include a step of chemically and/or mechanically removing the part of the silicon-containing thin film outside the contact
20 hole. The silicon-containing thin film after completing the step of removing the part of the silicon-containing thin film may be somewhat slightly raised above the edge of the contact hole or somewhat slightly recessed therefrom.

25 The abovementioned semiconductor substrate may

be provided with a plurality of cells each including such a contact hole. In this case, the ratio of the amount of silicon contained in the silicon-containing thin film per unit cell to
5 aluminum supplied to a unit cell in the step of forming the aluminum thin film may be not less than 0.1% and not more than 2% by atomic ratio.

By selecting the ratio of the amount of silicon to the amount of aluminum, the abovementioned
10 movement of aluminum atoms effectively occurs by diffusion, so that the contact hole can be suitably filled with the aluminum thin film. Further, formation of silicon nodules due to excessive silicon can be prevented. The atomic ratio of silicon
15 contained in the silicon-containing thin film to aluminum has to be within the abovementioned range only after completing the step of removing the part of the silicon-containing thin film, and it may be of a larger value immediately after the
20 silicon-containing thin film is formed.

The step of forming a silicon-containing thin film may include a step of forming a polysilicon thin film by chemical vapor deposition method.

A polysilicon film can be suitably filled in a
25 contact hole by chemical vapor deposition method.

The step of forming the aluminum thin film may include a step of forming an aluminum thin film by sputtering method which is an example of physical vapor deposition method.

5 The abovementioned step of heating the semiconductor substrate may includes a step of heating the semiconductor substrate to $380^{\circ}\text{C} \sim 570^{\circ}\text{C}$.

By heating the semiconductor substrate to a temperature not lower than 380°C in the step of
10 forming the aluminum thin film, aluminum atoms and silicon atoms can suitably diffuse as abovementioned, so that the aluminum thin film can be suitably filled into the contact hole.

Further, by selecting the heating temperature
15 of the semiconductor substrate not higher than 570°C , the amount of aluminum atoms diffusing from the aluminum thin film filled into the contact hole into the semiconductor substrate and the like can be reduced.

20 The abovementioned and other objects, features and advantages of the present invention will become more apparent from the following description of preferred embodiments given with reference to the appended drawings.

25 BRIEF DESCRIPTION OF THE DRAWING

Fig. 1 is a schematic sectional view showing a structure of a MOS FET manufactured by the method according to the present invention.

Figs. 2(a), 2(b), 2(c), 2(d) and 2(e) are
5 schematic sectional views for explaining a method for forming an aluminum electrode film.

DESCRIPTION OF THE PREFERRED EMBODIMENTS

Fig. 1 is a schematic sectional view showing a structure of a MOS FET (Metal Oxide Semiconductor
10 Field Effect Transistor) manufactured by the method according to the present invention.

An n^- -type epitaxial layer 2 is formed on the surface of a silicon substrate 1. A plurality of ridge-shaped stacked layers 3 are formed on the
15 epitaxial layer 2. The stacked layers 3 include ones extended in a first direction along the surface of the silicon substrate 1 (the direction perpendicular to the paper surface in Fig. 1) and ones extended in a second direction along the surface of the silicon
20 substrate 1 and perpendicular to the first direction (in parallel to the paper surface in Fig. 1). A plurality of stacked layers 3 are arranged substantially in parallel to each other with respect to the respective directions. In other words, the
25 stacked layers 3 are formed in a grid-like

arrangement. The region surrounded by the stacked layers 3 constitutes a contact hole 4. The contact hole 4 has a depth not reaching the epitaxial layer 2.

5 The stacked layer 3 includes a p^- -layer 5, an n^+ -layer 6 and a silicon oxide layer 7 stacked from the lower portion (the epitaxial layer 2 side) to the upper portion.

A polysilicon layer 8 is formed to extend from
10 the upper portion of the epitaxial layer 2 into the stacked layer 3. The polysilicon layer 8 penetrates the p^- -layer 5 and the n^+ -layer 6 and is in contact with the silicon oxide layer 7 at its upper side (the side opposite to the epitaxial layer 2 side). The
15 polysilicon layer 8 has been made conductive by adding impurities thereto, and externally connected at the end portion of the silicon substrate 1 so as to serve as a gate electrode of the FET.

An oxide layer (gate oxide layer) 9 is formed
20 surrounding the polysilicon layer 8 except the portion in contact with the silicon oxide layer 7.

At the bottom of the contact hole 4, a p^+ -layer
10 having a smaller thickness than that of the p^- -layer 5 is formed in contact with the epitaxial
25 layer 2 and between the p^- -layers 5 of the adjacent

stacked layers 3. On the stacked layers 3 and the p⁺-layer 10, an aluminum electrode film 11 containing aluminum (Al) as the main component is formed so as to fill the contact hole 4. The aluminum electrode film 11 contains a small amount (for example, 0.3% of the aluminum by atomic ratio) of silicon. The aluminum electrode film 11 functions as a deriving electrode of the n⁺-layer 6.

By applying a predetermined voltage between the aluminum electrode film 11 and an unshown electrode connected to the silicon substrate 1 and making the polysilicon layer 8 (gate electrode) at a predetermined potential, a current (drain current) can flow between the n⁺-layer 6 and the epitaxial layer 2 through the p⁻-layers 5. In the p⁻-layers 5, the drain current flows in the vicinity of and along the oxide layer 9. Therefore, a channel is formed in the vicinity of the oxide layer 9 in the p⁻-layer 5.

In the MOS FET having such a structure as abovementioned, the width W1 of the contact hole 4 is, for example, 0.6 μ m, and the ratio (aspect ratio) D/W1 of the depth D of the contact hole 4 to the width W1 thereof is large (for example, not less than 1). The width W2 of the polysilicon layer 8 is, for example,

0.6 μm , and the width W3 of the part of the stacked layer 3 on one side of the polysilicon layer 8 is, for example, 0.45 μm . Therefore, the width W4 of a device unit (cell C) of this MOS FET is, for example, 2.1 μm . Since the channel is formed in the vertical direction (in the direction perpendicular to the silicon substrate 1) and in addition, the n^+ -layer 6 and the aluminum electrode film 11 are in contact with each other on the inner wall of the contact hole 4, such a small cell C can be realized.

By making a cell C so small, a large number of cells C can be obtained in a unit area. Thereby, the number of the channels per unit area and regions in the epitaxial layer 2 in which the current flows can be increased. As a result, ON-state resistance can be reduced.

Figs. 2(a), 2(b), 2(c), 2(d) and 2(e) are schematic sectional views for explaining a step for forming an aluminum electrode film 11.

Firstly, a polysilicon film 15 is formed on the p^+ -layer 10 and the stacked layer 3 by CVD (chemical vapor deposition) method (see Fig. 2(a)). The polysilicon film 15 is formed with a thickness enough to fill the contact hole substantially on the whole surface of the silicon substrate.

Then, the part of the polysilicon film 15 outside the contact hole 4 is removed (etched back) so that the polysilicon film 15 exists only in the contact hole 4. This state is shown in Fig. 2(b). The polysilicon film 15 may be slightly raised above the edge of the contact hole 4 or slightly recessed therefrom. In order to obtain such a state of the polysilicon film 15, for example, the etching time has only to be controlled.

10 Next, aluminum atoms are deposited on the silicon substrate 1 on which the polysilicon film 15 is formed by sputter method to form an aluminum thin film 16. Aluminum atoms supplied onto the silicon substrate 1 by sputtering method are deposited
15 substantially uniformly on the stacked layer 3 and the polysilicon film 15 filling the contact hole 4 (see Fig. 2(c)).

Then, the silicon substrate 1 after the abovementioned steps is heated. The heating
20 temperature is $380^{\circ}\text{C} \sim 570^{\circ}\text{C}$. Thereby, aluminum atoms deposited on the polysilicon film 15 and the stacked layer 3 diffuse in the polysilicon film 15, or move into the contact hole 4. Further, silicon atoms constituting the polysilicon film 15 also diffuse in
25 the aluminum thin film 16.

In such a manner, the polysilicon film 15 in the contact hole 4 is gradually replaced by the aluminum thin film 16 (see Fig. 2(d)). After the silicon substrate 1 is heated for a suitable time, the contact hole 4 has been perfectly filled with the aluminum thin film 16. In such a manner, a preferable aluminum electrode film 11 having no void (air gap) can be obtained (see Fig. 2(e)). Such a manufacturing method is especially effective in case that the width or the diameter of the contact hole 4 is as small as not more than $0.6\ \mu\text{m}$ and the aspect ratio is as high as not less than 1.

The amount of silicon per unit cell C contained in the polysilicon film 15 (see Fig. 2(b)) after etching back with respect to the amount of aluminum per unit cell C supplied to the silicon substrate 1 by sputtering method is not less than 0.1% and not more than 2% by atom ratio. Thereby, the abovementioned movement of aluminum atoms effectively occurs by diffusion, so that the contact hole 4 can be suitably filled with the aluminum electrode film 11. Further, formation of silicon nodules due to excessive silicon can be prevented.

Therefore, the aluminum electrode film 11

contains aluminum as the main component and a little amount (for example, 0.3% of aluminum by atomic ratio) of silicon.

In the abovementioned manufacturing method, since the contact hole 4 has a predetermined volume, the amount of the polysilicon film 15 or the amount of polysilicon in the polysilicon film 15 after etching back can be accurately controlled.

Further, the ratio of the amount of silicon after etching back to the amount of the aluminum supplied to the silicon substrate 1 is preferably within the solid solubility limit of silicon with respect to aluminum at the temperature used in the step of heating the silicon substrate 1. In this case, whole of silicon atoms constituting the polysilicon film 15 move into the aluminum thin film 16, and after completing the formation of the aluminum thin film 16, the polysilicon film 15 does not exist between the aluminum thin film 16 (aluminum electrode film 11) and the p⁺-layer 10 and the stacked layer 3.

After the aluminum electrode film 11 is formed, unnecessary portions of the aluminum electrode film 11 are removed away by etching or the like.

Since the aluminum electrode film 11 contains silicon within the solid solubility limit, aluminum

atoms constituting the aluminum electrode film 11 are hard to diffuse in the p^+ -layer 10, the stacked layer 3, the epitaxial layer 2 and the like even if the silicon substrate 1 is heated to a high temperature at the time of forming the aluminum electrode film 11 by sputtering method or in any other step. Therefore, destruction of p-n junction by the diffusion of aluminum atoms into the epitaxial layer 2, the p^- -layer 5 and the n^+ -layer 6 constituting a device can be prevented.

Further, in case of forming the aluminum electrode film 11 in such a manner, it is not necessary to form a barrier metal layer before forming the aluminum electrode film 11.

Though one embodiment of the present invention has been explained as above, other embodiments of the present invention are possible. For example, a method for manufacturing a semiconductor device according to the present invention can be applied to cases of forming thin films by filling various contact holes of semiconductor devices other than a MOS FET.

For example, in the abovementioned embodiment, the aluminum electrode film 11 is electrically connected to the n^+ -layer 6 (semiconductor layer) exposed to the side surface of the contact hole 4.

However, the aluminum electrode film 11 may be formed to be electrically connected to a semiconductor layer (including the substrate itself) exposed to the bottom surface of the contact hole 4. In this case, 5 only an insulator may be exposed to the inner side wall of the contact hole 4.

Further, the contact hole 4 is not limited to one for connecting a deriving electrode to a semiconductor layer (device) but may be one for 10 effecting inter-layer connection of wirings (for example, metal wirings). In this case, the wirings are exposed to the inside (for example, the bottom surface) of the contact hole 4 and the aluminum electrode film 11 can be filled into the contact hole 15 4 by the same method as that of the abovementioned embodiment.

Further, the aluminum electrode film 11 may be one electrically connected to a conductor exposed to the inside of the contact hole 4.

20 The contact hole into which a thin film (electrode wiring) is filled is not limited to one having a width or diameter not more than $0.6 \mu\text{m}$ but may have a width or diameter more than $0.6 \mu\text{m}$. Furthermore, the contact hole into which a thin film 25 (electrode wiring) is filled is not limited to one

having an aspect ratio not less than 1 but may have an aspect ratio less than 1.

The semiconductor device may be another than a MOS FET such as IGBT (Insulated Gate Bipolar Transistor).

The process of heating the silicon substrate 1 (see Fig. 2(d)) may be carried out at the same time with the step of depositing aluminum atoms on the silicon substrate 1 (see Fig. 2(c)). That is, sputtering of the aluminum may be carried out with heating the silicon substrate 1. In this case, heating of the silicon substrate 1 may be continued for a suitable time after stopping supplying aluminum atoms onto the silicon substrate 1.

While the present invention has been described in detail by way of the embodiment thereof, it should be understood that the foregoing disclosure is merely illustrative of the technical principles or the present invention but not limitative of the same. The spirit and scope of the present invention are to be limited only by the appended claims.

This application corresponds to Japanese Patent Application No. 2003-51572 filed with the Japanese Patent Office on February 27, 2003, the disclosure of which is incorporated herein by reference.